MOSFET – Power, Dual N-Channel, SO-8FL 60 V, 22.6 mΩ, 24 A

NVMFD024N06C

Features

- Small Footprint (5x6 mm) for Compact Design
- Low R_{DS(on)} to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- NVMFWD024N06C Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Power Tools, Battery Operated Vacuums
- UAV/Drones, Material Handling
- BMS/Storage, Home Automation

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Units
Drain-to-Source Voltage			V_{DSS}	60	V
Gate-to-Source Volta	Gate-to-Source Voltage			±20	V
Continuous Drain	Steady State	T _C = 25°C	I _D	24	Α
Current ReJC (Note 1,3)	State	T _C = 100°C		17	
Power Dissipation	, ,		P_{D}	28	W
ReJC (Note 1)	State	T _C = 100°C		14	
Continuous Drain Current Reja			I _D	8	Α
(Note 1, 2,3)	State	T _A = 100°C		5	
Power Dissipation	Power Dissipation ReJA (Note 1, 2) State $T_A = 25^{\circ}C$ $T_A = 100^{\circ}C$		P _D	3.1	W
HeJA (Note 1, 2)				1.5	
Pulsed Drain Cur- rent	$T_A = 25^{\circ}C$, $t_p = 10 \mu s$		I _{DM}	85	Α
Operating Junction and Storage Temperature			T _J , T _{stg}	-55 to 175	°C
Source Current (Body Diode)			I _S	23	Α
Single Pulse Drain-to-Source Avalanche Energy ($I_L = 5.3 \; A_{pk}$)			E _{AS}	14	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
- 2. Surface-mounted on FR4 board using a 650 mm², 2 oz Cu pad.
- 3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

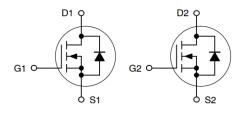


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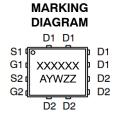
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V _{(BR)DSS}	R _{DS(ON)} MAX	I _D MAX	
60 V	22.6 m Ω @ 10 V	24 A	

Dual N-Channel







XXXXXX = 24DN6C

(NVMFD024N06C) or

24DN6W

(NVMFWD024N06C)

A = Assembly Location

Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case - Steady State (Note 2)	$R_{ heta JC}$	5.3	°C/W
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	46.9	*C/VV

ELECTRICAL CHARACTERISTICS (T_{.1} = 25°C unless otherwise specified)

Parameter	Symbol	Test Con	dition	Min	Тур	Max	Unit
OFF CHARACTERISTICS							-
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	I_D = 250 μ A, ref to 25°C			27		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	I_{DSS} $V_{GS} = 0 V$, $T_{J} = 25^{\circ}C$				10	μΑ
		V _{DS} = 60 V	T _J = 125°C			250	1
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V	_{GS} = 20 V			100	nA
ON CHARACTERISTICS (Note 3)							-
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I	D = 20 μA	2.0		4.0	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /	I _D = 20 μA, r	ef to 25°C		-7.8		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V,	I _D = 3 A		18.8	22.6	mΩ
Forward Transconductance	9FS	V _{DS} = 5 V,	I _D = 3 A		10		S
Gate Resistance	R _G	T _A = 2	5°C		0.8		Ω
CHARGES & CAPACITANCES				•		•	•
Input Capacitance	C _{ISS}				333		
Output Capacitance	C _{OSS}	V _{GS} = 0 V, f = 1 M	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 30 V		225		pF
Reverse Capacitance	C _{RSS}				5.05		
Total Gate Charge	Q _{G(TOT)}	$V_{GS} = 10 \text{ V}, V_{DS} = 48 \text{ V}, I_D = 3 \text{ A}$			5.7		
Threshold Gate Charge	Q _{G(TH)}				1.3		nC
Gate-to-Source Charge	Q _{GS}				2.0		
Gate-to-Drain Charge	Q _{GD}				0.68		
SWITCHING CHARACTERISTICS (Note	3)			•	•		•
Turn-On Delay Time	t _{d(ON)}				6.6		
Rise Time	t _r	V _{GS} = 10 V. V	/ne = 48 V.		1.3		ns
Turn-Off Delay Time	t _{d(OFF)}	V _{GS} = 10 V, V I _D = 3 A, R	$G = 6 \Omega$		10		
Fall Time	t _f				3		1
DRAIN-SOURCE DIODE CHARACTERIS	STICS			ı		l	
		V _{GS} = 0 V,	T _J = 25°C		0.8	1.2	
Forward Voltage	V _{SD}	I _S = 3 A	T _J = 125°C		0.66		V
Reverse Recovery Time	t _{RR}		1		23		
Charge Time	ta	$V_{GS} = 0 \text{ V, } d_{IS}/d_t = 100 \text{ A}/\mu\text{s,}$ $V_{DS} = 30 \text{ V, } I_S = 3 \text{ A}$			11		ns
Discharge Time	tb				12		
Reverse Recovery Charge	Q _{RR}				11		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

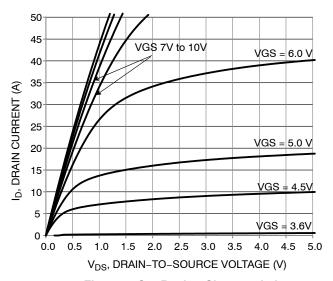


Figure 1. On-Region Characteristics

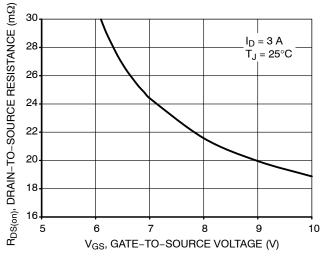


Figure 3. On-Resistance vs. Gate-to-Source Voltage

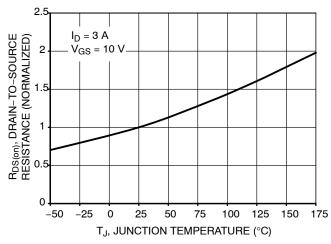


Figure 5. On–Resistance Variation with Temperature

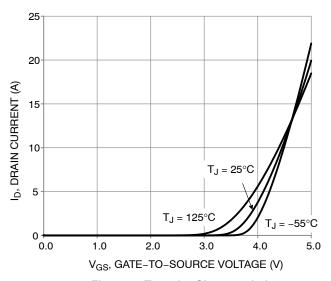


Figure 2. Transfer Characteristics

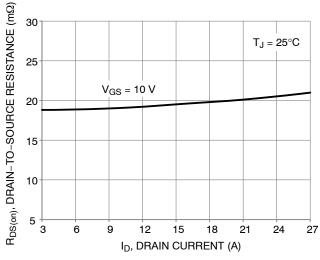


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

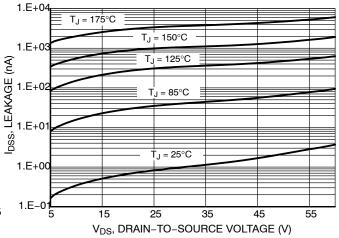


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

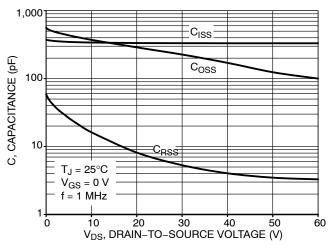


Figure 7. Capacitance Variation

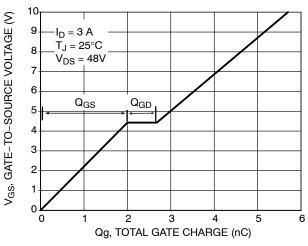


Figure 8. Gate-to-Source vs. Total Charge

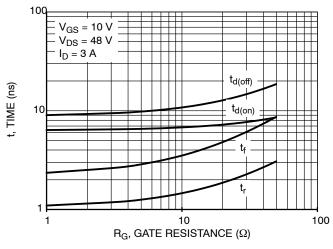


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

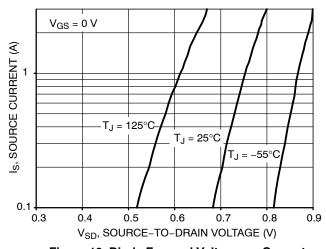


Figure 10. Diode Forward Voltage vs. Current

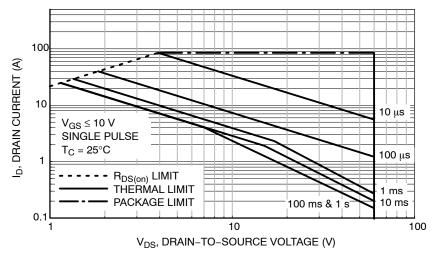


Figure 11. Maximum Rated Forward Biased Safe Operating Area

TYPICAL CHARACTERISTICS

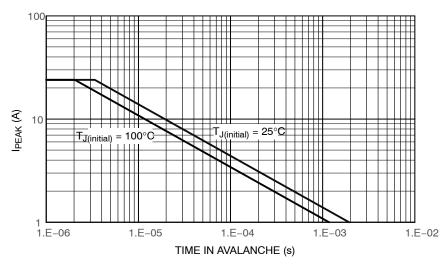


Figure 12. Maximum Drain Current vs. Time in Avalanche

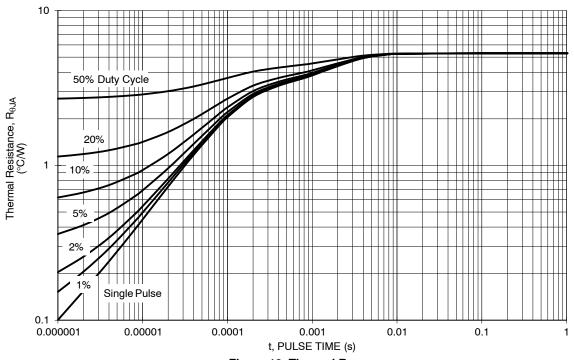


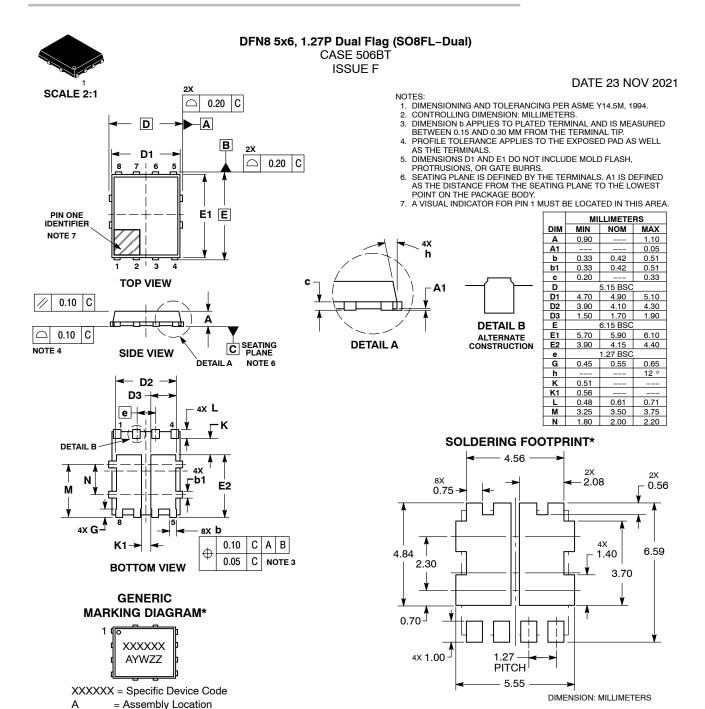
Figure 13. Thermal Response

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVMFD024N06CT1G	24DN6C	DFN8 (Pb-Free)	1500 / Tape & Reel
NVMFWD024N06CT1G	24DN6W	DFN8 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





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DESCRIPTION:	DFN8 5X6, 1.27P DUAL FLAG (SO8FL-DUAL)		PAGE 1 OF 1		

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= Year

not follow the Generic Marking.

= Work Week

= Lot Traceability *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may

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W

ZZ

*For additional information on our Pb-Free strategy and soldering

Mounting Techniques Reference Manual, SOLDERRM/D.

details, please download the ON Semiconductor Soldering and

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